

PATENT ABSTRACTS OF JAPAN

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(54) METHOD FOR PROCESSING FILM AND METHOD FOR MANUFACTURING
SEMICONDUCTOR DEVICE USING THE SAME

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a method for processing a film wherein a silica film (interlayer insulating film) is hardly damaged in ashing a resist pattern.

SOLUTION: The silica type film with a low dielectric constant formed on a substrate is etched using the resist pattern. Then the silica type film subsequent to the etching process is treated by a plasma induced by a mixing gas of nitrogen and hydrogen or by an ammonia gas. Thus, the silica type film is not damaged in the post-process of ashing the resist pattern and the low dielectric constant can be maintained.

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